REMARKS

Entry of this Amendment and reconsideration of this application, as amended, are respectfully requested. By this Amendment, the feature that was the basis for the sole remaining rejection has been deleted from independent claim 1, and an aspect of the invention that was implicit in previously presented claim 31 has been incorporated into independent claim 1. The addition of "new matter" has been scrupulously avoided. Claims 1-27 and 29-31 remain in this case.

In the last Office Action, claims 1-27 and 29-31 were rejected under 35 U.S.C. 112, first paragraph, as allegedly failing to comply with the written description requirement. More specifically, the Examiner asserted that there is no description in the disclosure as originally filed of "the p-doped or n-doped inner area having a same doping concentration as the starting semiconductor substrate".

While disagreeing with this assertion, Applicant has, for the sake of expediting allowance of this application, deleted the specified feature from independent claim 1 and, therefore, implicitly from all of the pending claims.

Instead, amended claim 1 now specifies that the starting semiconductor substrate and remaining inner area are weakly doped. Dependent claim 31 specifies that the starting semiconductor substrate and inner area have a low doping concentration (p-) or (n-).

The term weakly doped is used in the original specification, e.g. in the last paragraph on page 1 and the bottom half of page 5, and the corresponding low doping concentration (p-) for the starting substrate and remaining inner area are clearly shown in all of the original drawing figures.

Accordingly, Applicant respectfully submits that there is no remaining issue of the presently presented claims failing to comply with the written description requirement.

Furthermore, there are no prior art or other grounds for rejection of the claims in the last Office Action.

Finally, Applicant submits that the current amendments to claims 1 and 31 do not raise new issues that would require further search or examination since the current amendments merely incorporate a limitation into claim 1 that was contained in former claim 31. Previously presented claim 31 stated that the starting semiconductor substrate has a low doping

concentration as the starting semiconductor substrate. Accordingly, Applicant respectfully submits that the amendment to independent claim 1 that explicitly states that the starting substrate and inner area are weakly doped is not a new limitation requiring further search or examination.

For the above reasons, all of the claims in this application are believed to be in condition for allowance and such action is respectfully requested.

Should the Examiner continue to entertain any reservations, he is requested to call Applicant's representative at the below indicated telephone number to discuss and resolve same.

Respectfully submitted,

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